

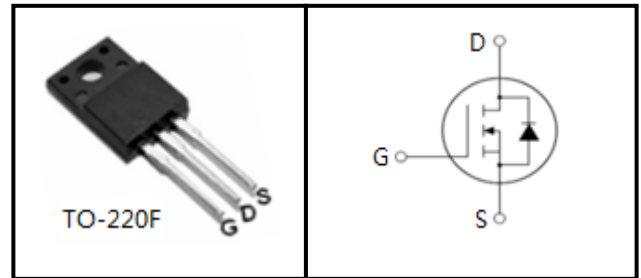
## 650V N-Channel MOSFET

### FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



### Device Marking and Package Information

Device	Package	Marking
CS10N65FF	TO-220F	CS10N65FF

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-220F	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	650	V
Continuous Drain Current	$I_D$	10	A
Pulsed Drain Current (note1)	$I_{DM}$	40	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	304	mJ
Avalanche Current (note1)	$I_{AS}$	7.8	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	182.4	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	65	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

### Thermal Resistance

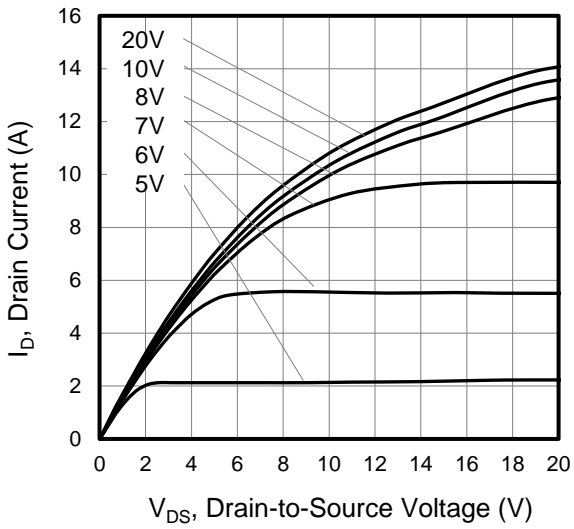
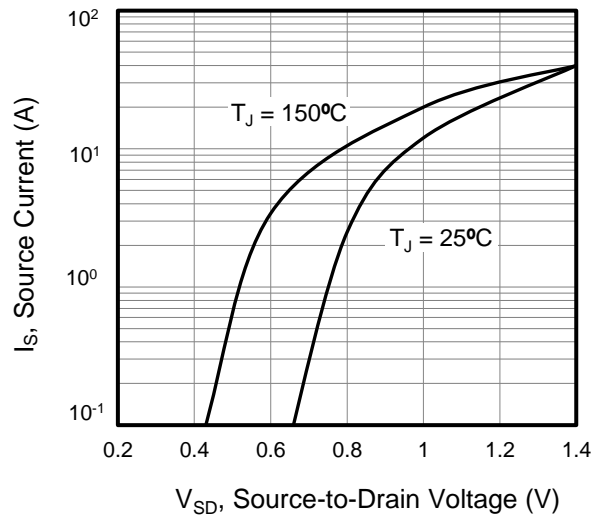
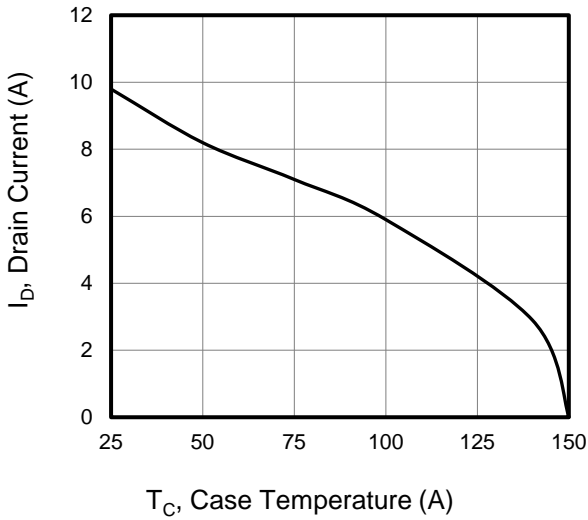
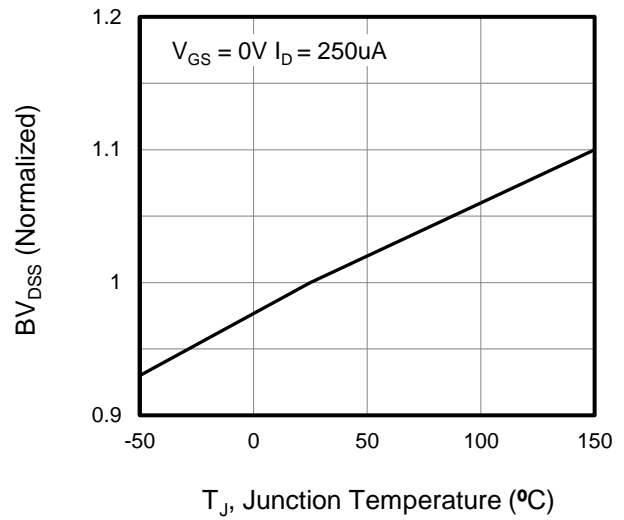
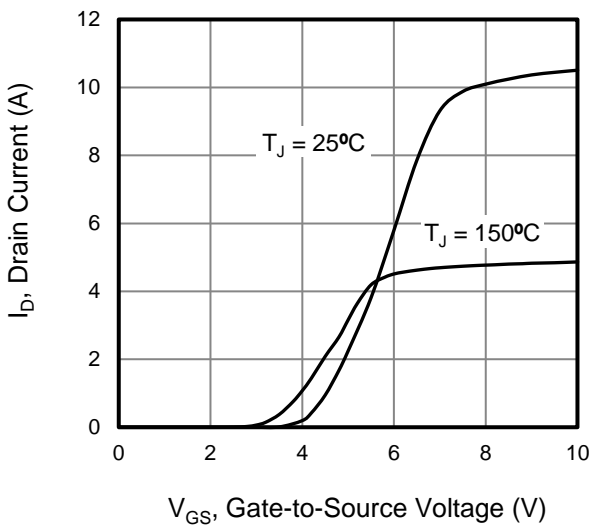
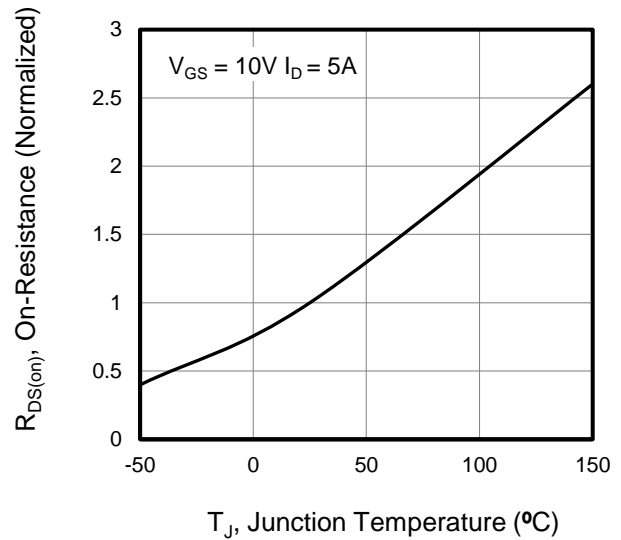
Parameter	Symbol	Value	Unit
		TO-220F	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.92	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	

Specifications $T_J = 25^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^{\circ}\text{C}$	--	--	1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.0A$	--	0.65	0.8	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	1507	--	pF
Output Capacitance	$C_{oss}$		--	135	--	
Reverse Transfer Capacitance	$C_{rss}$		--	3.8	--	
Internal Gate Resistance	$R_g$		--	1.1	--	$\Omega$
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 10A,$ $V_{GS} = 10V$	--	28	--	nC
Gate-Source Charge	$Q_{gs}$		--	7.3	--	
Gate-Drain Charge	$Q_{gd}$		--	10	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 325V, I_D = 10A,$ $R_G = 25\Omega$	--	43.3	--	ns
Turn-on Rise Time	$t_r$		--	17.3	--	
Turn-off Delay Time	$t_{d(off)}$		--	112	--	
Turn-off Fall Time	$t_f$		--	35.4	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^{\circ}\text{C}$	--	--	10	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	40	
Body Diode Voltage	$V_{SD}$	$T_J = 25^{\circ}\text{C}, I_{SD} = 5A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 325V, I_S = 10A,$ $di_F/dt = 100A/\mu s$	--	310	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	3.6	--	$\mu C$

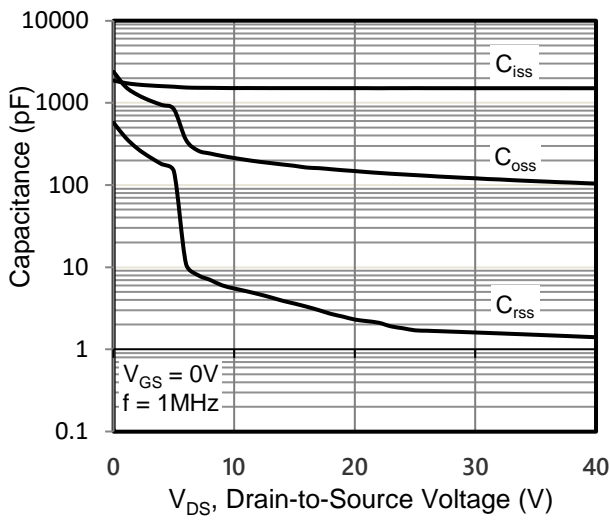
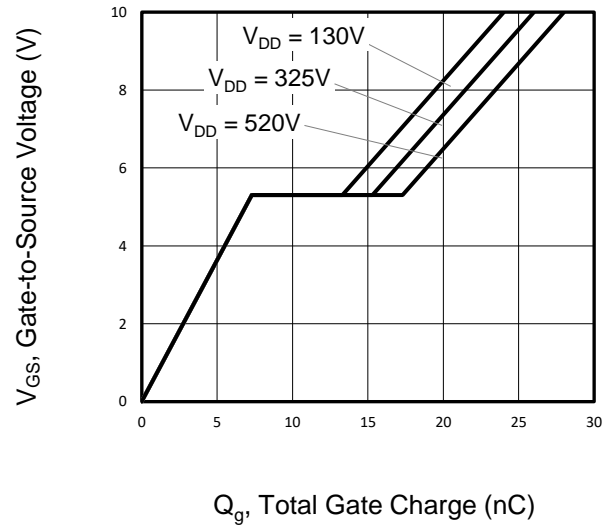
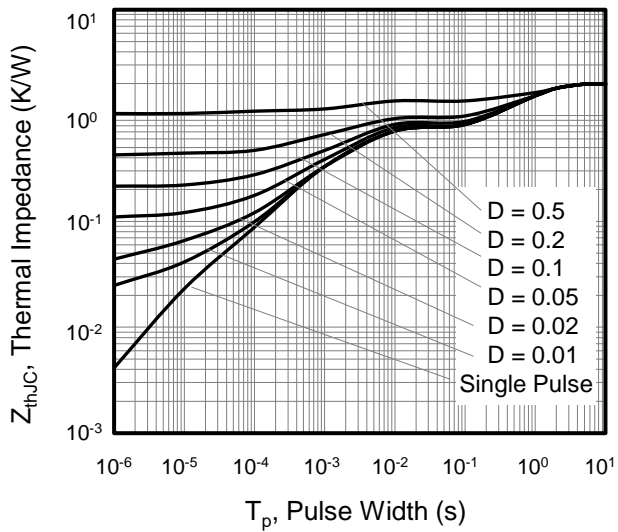
**Notes**

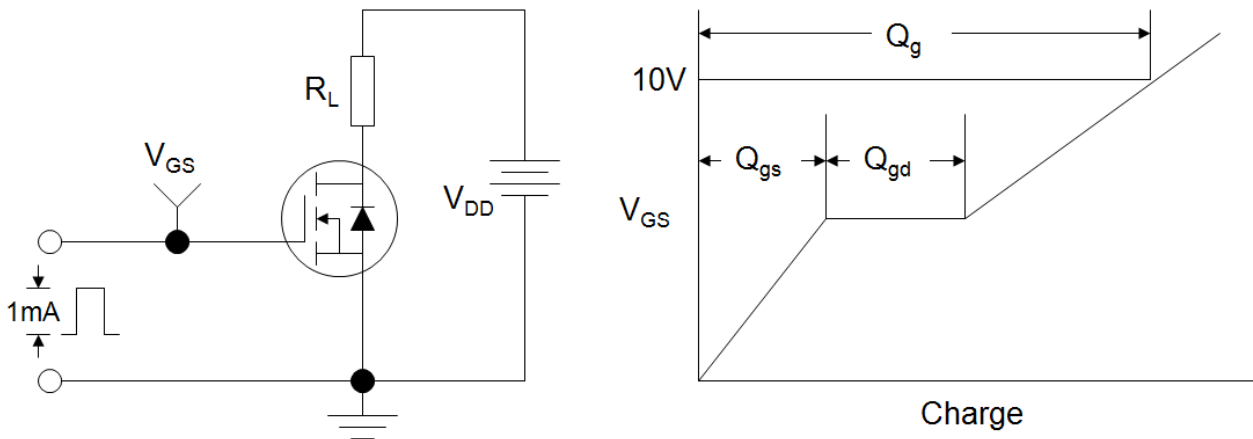
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L=10\text{mH}, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

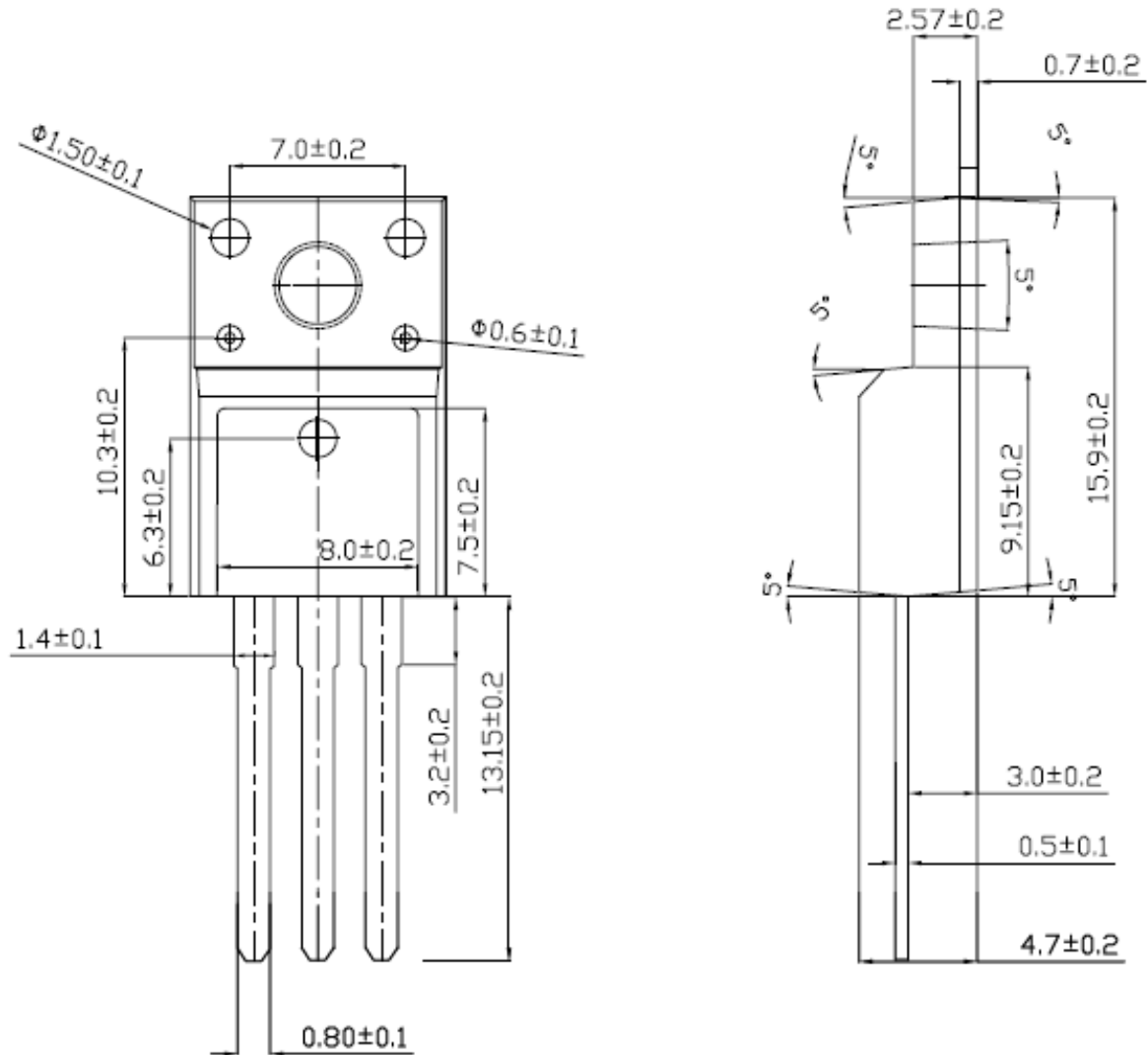
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**

**Figure 2. Body Diode Forward Voltage**

**Figure 3. Drain Current vs. Temperature**

**Figure 4.  $BV_{DSS}$  Variation vs. Temperature**

**Figure 5. Transfer Characteristics**

**Figure 6. On-Resistance vs. Temperature**


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

**Figure 7. Capacitance**

**Figure 8. Gate Charge**

**Figure 9. Transient Thermal Impedance**
**TO-220F**


**Figure A: Gate Charge Test Circuit and Waveform**

**Figure B: Resistive Switching Test Circuit and Waveform**

**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**


**TO-220F**


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